

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CMPD3003
CMPD3003A
CMPD3003C
CMPD3003S

SURFACE MOUNT
LOW LEAKAGE
SWITCHING DIODE

SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPD3003 series types are silicon switching diodes manufactured by the epitaxial planar process, designed for switching applications requiring a extremely low leakage diode.

The following configurations are available:

CMPD3003	SINGLE
CMPD3003A	DUAL, COMMON ANODE
CMPD3003C	DUAL, COMMON CATHODE
CMPD3003S	DUAL, IN SERIES

MARKING CODE: LLO
MARKING CODE: LLA
MARKING CODE: LLC
MARKING CODE: LLS

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V _R	180	V
Average Rectified Current	I _O	200	mA
DC Forward Current	I _F	600	mA
Peak Repetitive Forward Current	I _{FRM}	700	mA
Peak Forward Surge Current, tp=1 s	I _{FSM}	1.0	A
Peak Forward Surge Current, tp=1 μs	I _{FSM}	2.0	A
Power Dissipation	P _D	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	357	°C/W

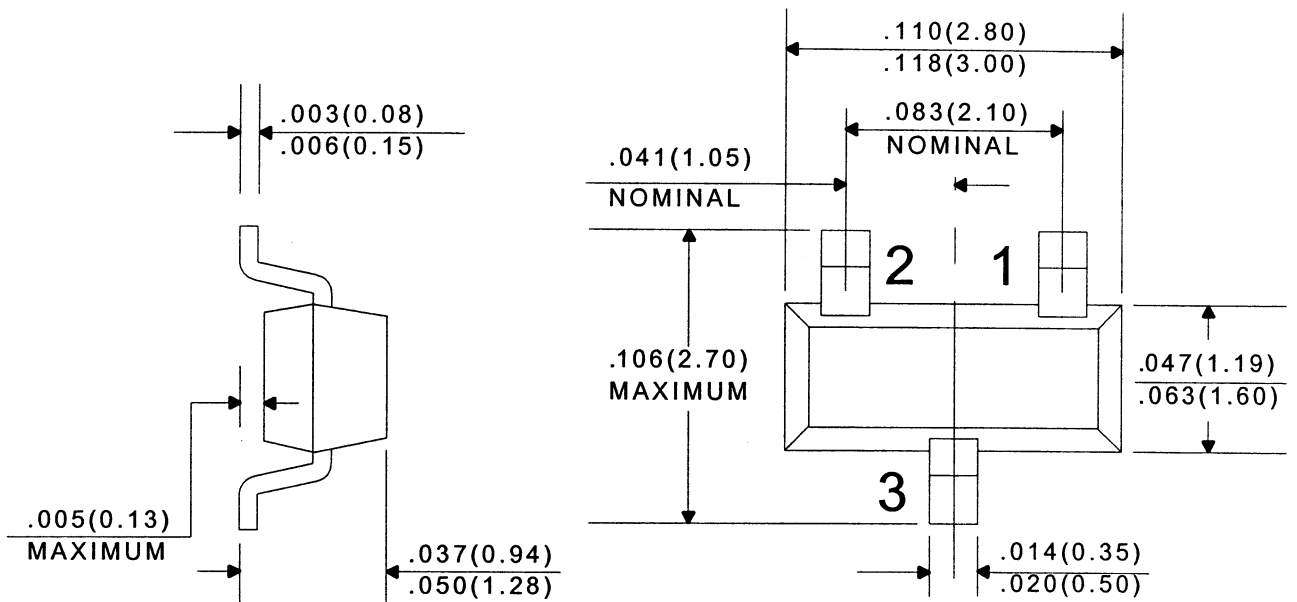
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
B _{VR}	I _R =5.0μA	200		V
I _R	V _R =125V		1.0	nA
I _R	V _R =125V, T _A =150°C		3.0	μA
I _R	V _R =180V		10	nA
I _R	V _R =180V, T _A =150°C		5.0	μA
V _F	I _F =1.0mA	0.62	0.72	V
V _F	I _F =10mA	0.72	0.83	V
V _F	I _F =50mA	0.80	0.89	V
V _F	I _F =100mA	0.83	0.93	V
V _F	I _F =200mA	0.87	1.10	V
V _F	I _F =300mA	0.90	1.15	V
C _J	V _R =0, f=1 MHz		4.0	pF

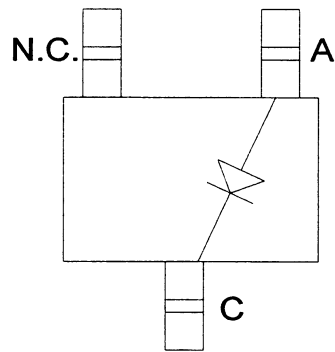
(See Reverse Side)



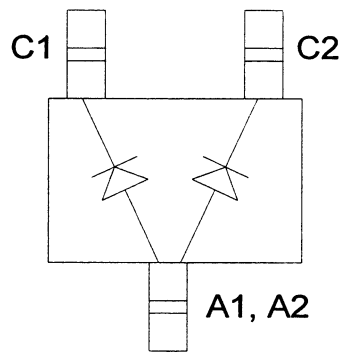
SOT-23 CASE - MECHANICAL OUTLINE



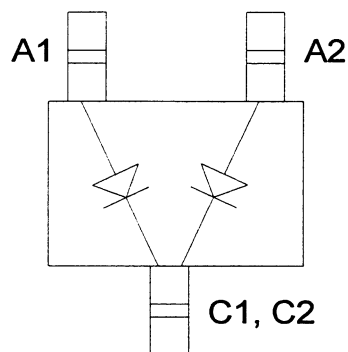
ALL DIMENSIONS IN INCHES (mm).



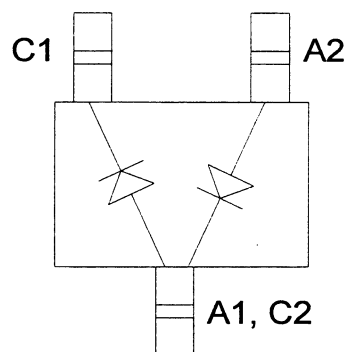
CMPD3003



CMPD3003A



CMPD3003C



CMPD3003S